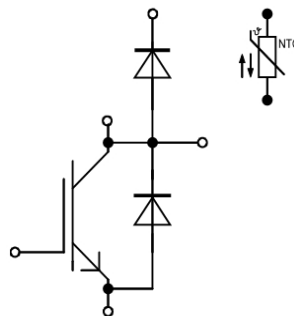


PrimePACK™3 模块 采用第四代沟槽栅/场终止IGBT4和发射极控制二极管
 PrimePACK™3 module with Trench/Fieldstop IGBT4 and Emitter Controlled diode



$V_{CES} = 1700V$
 $I_{C\ nom} = 1000A / I_{CRM} = 2000A$

潜在应用

- 三电平应用
- 大功率变流器
- 斩波应用
- 风力发电机

电气特性

- $T_{vj\ op} = 150^{\circ}C$
- 低 V_{CEsat}
- 低开关损耗
- 提高工作结温 $T_{vj\ op}$
- 高电流密度
- 高直流电压稳定性

机械特性

- 封装的 CTI > 400
- 标准封装
- 铜基板
- 高功率密度
- 高功率循环和温度循环能力
- 高爬电距离和电气间隙

Potential Applications

- 3-level-applications
- High power converters
- Chopper applications
- Wind turbines

Electrical Features

- $T_{vj\ op} = 150^{\circ}C$
- Low V_{CEsat}
- Low switching losses
- Extended operating temperature $T_{vj\ op}$
- High current density
- High DC stability

Mechanical Features

- Package with CTI > 400
- Standard housing
- Copper base plate
- High power density
- High power and thermal cycling capability
- High creepage and clearance distances

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 制动-斩波器 / IGBT, Brake-Chopper

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1700	V
连续集电极直流电流 Continuous DC collector current	$T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	I_{CDC}	1000	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	2000	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 1000\text{ A}$ $V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{ sat}}$	2,00 2,35 2,45	2,45 2,80 2,95	V V V
栅极阈值电压 Gate threshold voltage	$I_C = 36,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		V_{GEth}	5,20	5,80 6,40	V
栅极电荷 Gate charge	$V_{GE} = -15 / 15\text{ V}$		Q_G	10,0		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		R_{Gint}	1,5		Ω
输入电容 Input capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{ies}	81,0		nF
反向传输电容 Reverse transfer capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		C_{res}	2,60		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{CES}		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,55 0,60 0,60		μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,10 0,12 0,12		μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 1,8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	1,00 1,25 1,30		μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 1,8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,29 0,50 0,59		μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}, L_{\sigma} = 30\text{ nH}$ $di/dt = 8000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 1,2\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	265 390 415		mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 1000\text{ A}, V_{CE} = 900\text{ V}, L_{\sigma} = 30\text{ nH}$ $du/dt = 3000\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 1,8\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	200 295 330		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 1000\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		I_{SC}	4000		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		24,0	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$		R_{thCH}	9,00		K/kW
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

二极管，制动-斩波器 / Diode, Brake-Chopper

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
连续正向直流电流 Continuous DC forward current		I_F	1000	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	2000	A
I_{2t} -值 I_{2t} - value	$V_R = 0\text{ V}$, $t_P = 10\text{ ms}$, $T_{vj} = 125^{\circ}\text{C}$	I_{2t}	140	kA^2s
最大损耗功率 Maximum power dissipation	$T_{vj} = 150^{\circ}\text{C}$	P_{RQM}	1000	kW

特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 1000\text{ A}$, $V_{GE} = 0\text{ V}$ $T_{vj} = 25^{\circ}\text{C}$ $I_F = 1000\text{ A}$, $V_{GE} = 0\text{ V}$ $T_{vj} = 125^{\circ}\text{C}$ $I_F = 1000\text{ A}$, $V_{GE} = 0\text{ V}$ $T_{vj} = 150^{\circ}\text{C}$	V_F		1,85 1,95 1,95	2,25 2,35 2,35	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 1000\text{ A}$, $-di_F/dt = 8000\text{ A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $T_{vj} = 25^{\circ}\text{C}$ $V_R = 900\text{ V}$ $T_{vj} = 125^{\circ}\text{C}$ $V_{GE} = -15\text{ V}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}		1050 1200 1250		A A A
恢复电荷 Recovered charge	$I_F = 1000\text{ A}$, $-di_F/dt = 8000\text{ A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $T_{vj} = 25^{\circ}\text{C}$ $V_R = 900\text{ V}$ $T_{vj} = 125^{\circ}\text{C}$ $V_{GE} = -15\text{ V}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r		245 410 480		μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 1000\text{ A}$, $-di_F/dt = 8000\text{ A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) $T_{vj} = 25^{\circ}\text{C}$ $V_R = 900\text{ V}$ $T_{vj} = 125^{\circ}\text{C}$ $V_{GE} = -15\text{ V}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}		115 205 245		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode	R_{thJC}			48,0	K/kW
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		18,0		K/kW
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}		5,00		$\text{k}\Omega$
R100 偏差 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}$, $R_{100} = 493\text{ }\Omega$	$\Delta R/R$	-5		5	%
耗散功率 Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

根据应用手册标定

Specification according to the valid application note.

模块 / Module

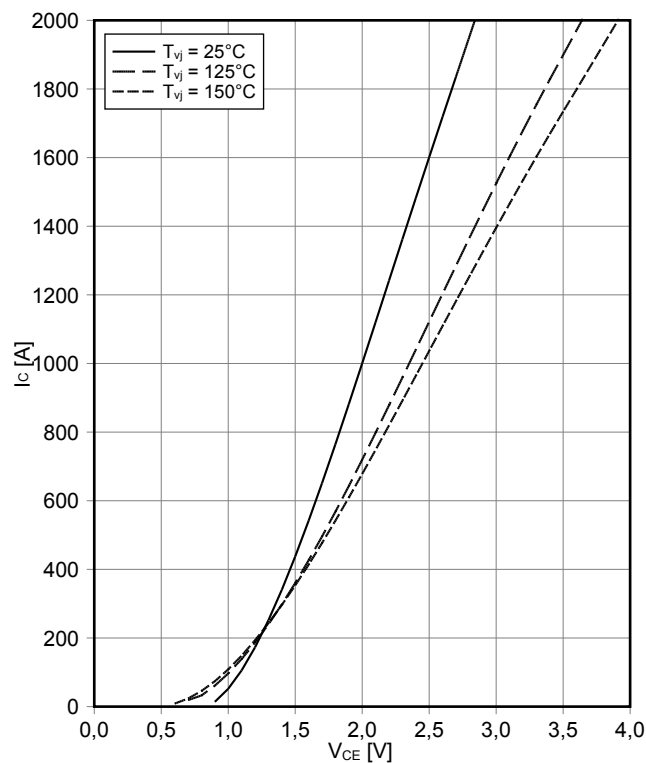
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	4,0	kV
模块基板材料 Material of module baseplate			Cu	
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		33,0 33,0	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		19,0 19,0	mm
相对电痕指数 Comperative tracking index		CTI	> 400	
min. typ. max.				
杂散电感, 模块 Stray inductance module		L _{sCE}		10 nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _c = 25°C, 每个开关 / per switch	R _{CC'+EE'}		0,20 mΩ
储存温度 Storage temperature		T _{stg}	-40	150 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00	6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M4 根据相应的应用手册进行安装 Screw M4 - Mounting according to valid application note	M	1,8	- 2,1 Nm
	螺丝 M8 根据相应的应用手册进行安装 Screw M8 - Mounting according to valid application note		8,0	- 10 Nm
重量 Weight		G		1200 g

输出特性 IGBT, 制动-斩波器 (典型)

output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$

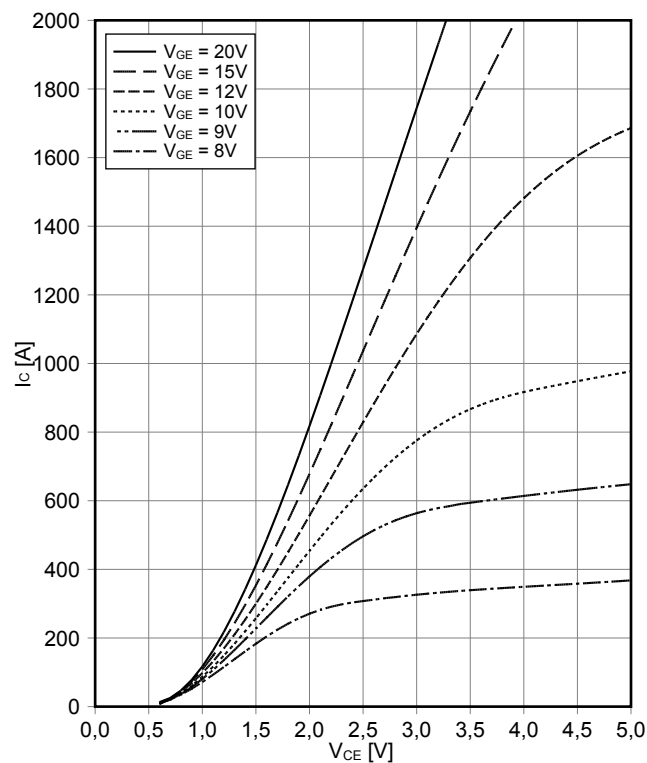


输出特性 IGBT, 制动-斩波器 (典型)

output characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{CE})$

$T_{vj} = 150^\circ\text{C}$

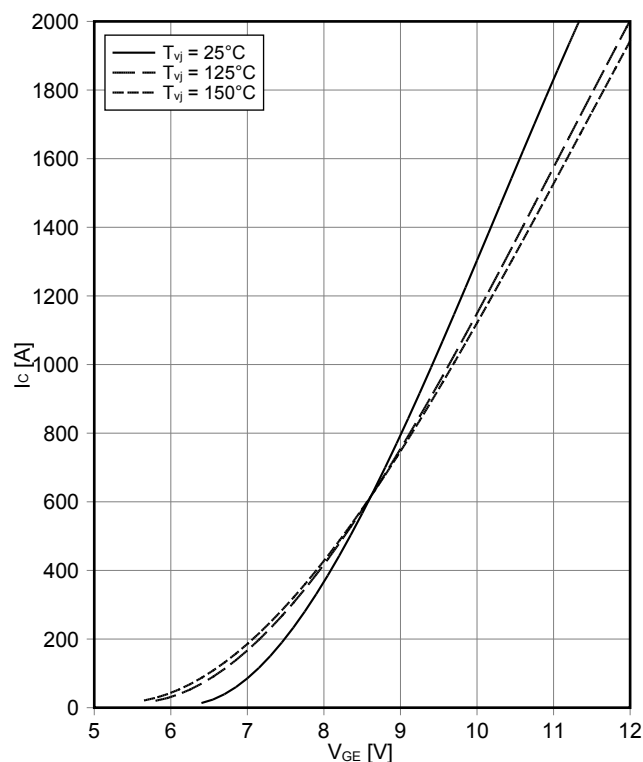


传输特性 IGBT, 制动-斩波器 (典型)

transfer characteristic IGBT, Brake-Chopper (typical)

$I_C = f(V_{GE})$

$V_{CE} = 20\text{ V}$

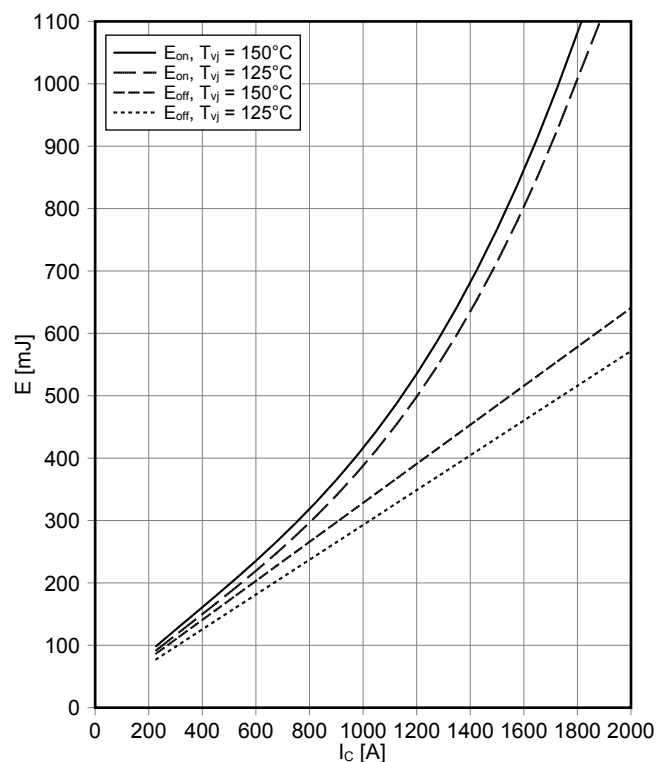


开关损耗 IGBT, 制动-斩波器 (典型)

switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$

$V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1.2\ \Omega$, $R_{Goff} = 1.8\ \Omega$, $V_{CE} = 900\text{ V}$

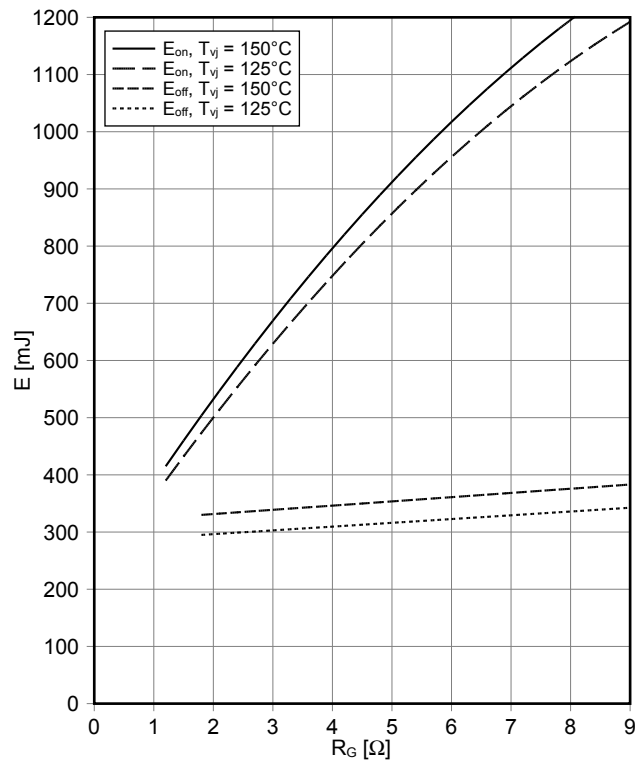


开关损耗 IGBT, 制动-斩波器 (典型)

switching losses IGBT, Brake-Chopper (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$

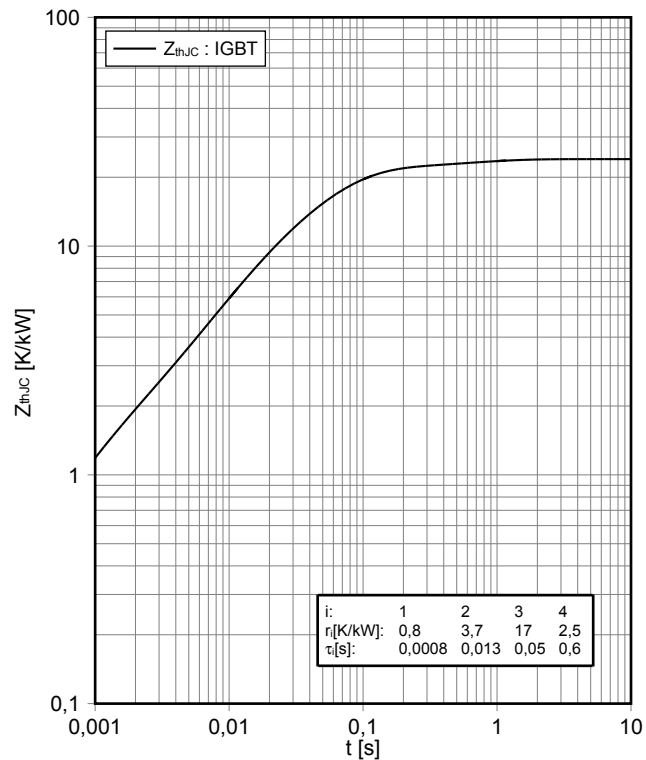
$V_{GE} = \pm 15 \text{ V}$, $I_C = 1000 \text{ A}$, $V_{CE} = 900 \text{ V}$



瞬态热阻抗 IGBT, 制动-斩波器

transient thermal impedance IGBT, Brake-Chopper

$Z_{thJC} = f(t)$

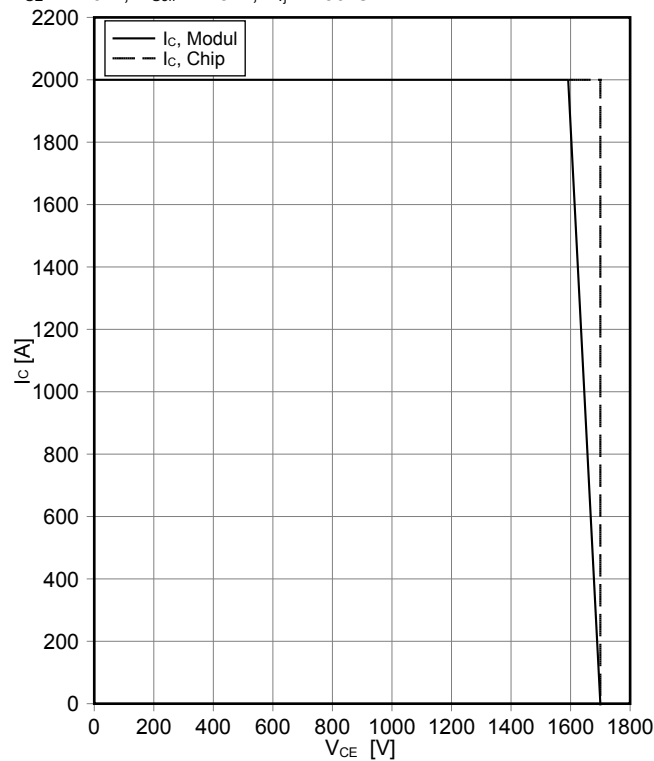


反偏安全工作区 IGBT, 制动-斩波器 (RBSOA)

reverse bias safe operating area IGBT, Brake-Chopper (RBSOA)

$I_C = f(V_{CE})$

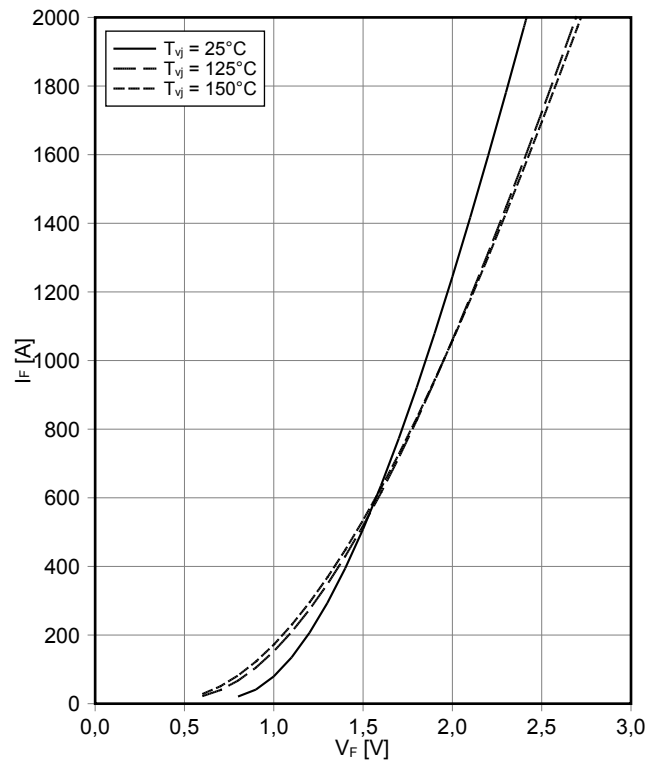
$V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 1.8 \Omega$, $T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 制动-斩波器 (典型)

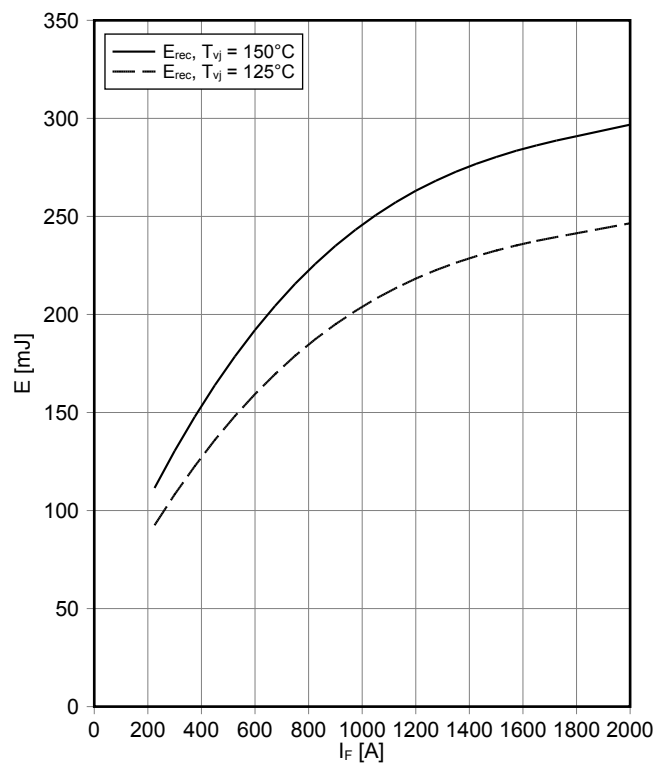
forward characteristic of Diode, Brake-Chopper (typical)

$I_F = f(V_F)$



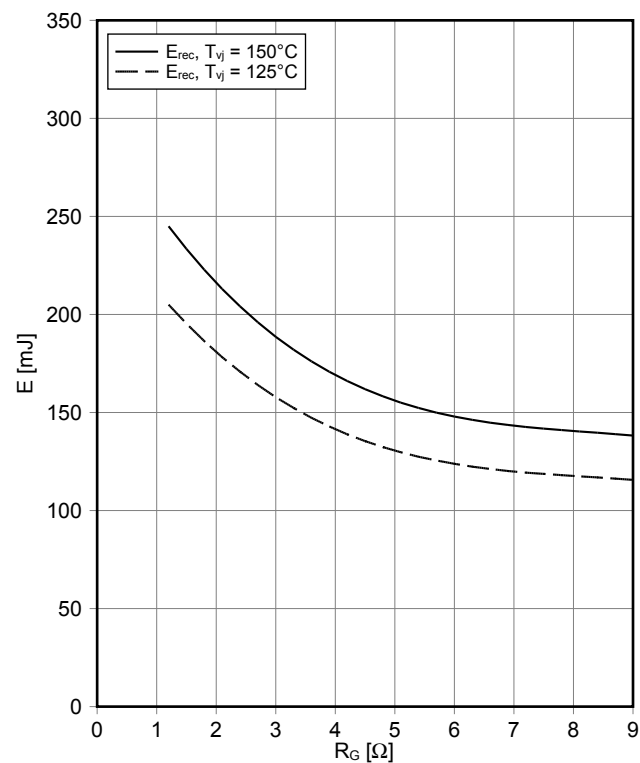
开关损耗 二极管，制动-斩波器（典型）

switching losses Diode, Brake-Chopper (typical)

 $E_{rec} = f(I_F)$ $R_{Gon} = 1.2 \Omega$, $V_{CE} = 900 V$ 

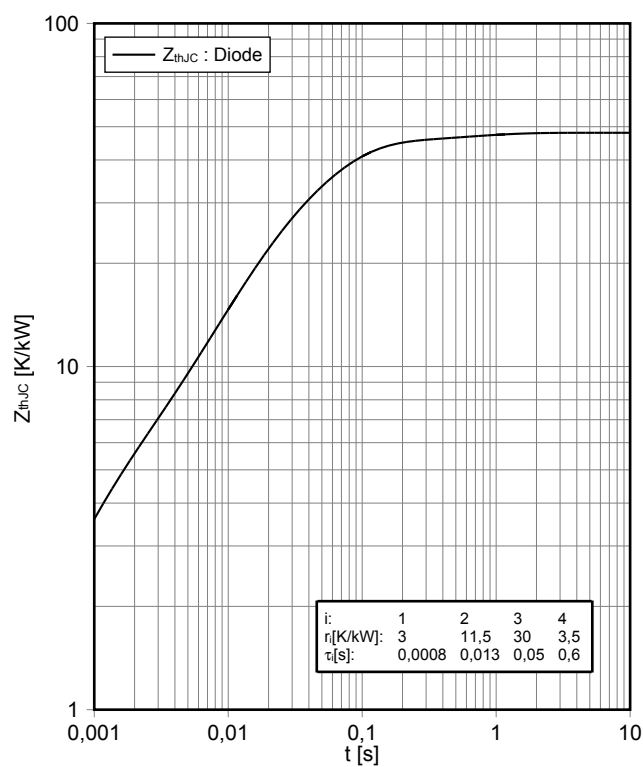
开关损耗 二极管，制动-斩波器（典型）

switching losses Diode, Brake-Chopper (typical)

 $E_{rec} = f(R_G)$ $I_F = 1000 A$, $V_{CE} = 900 V$ 

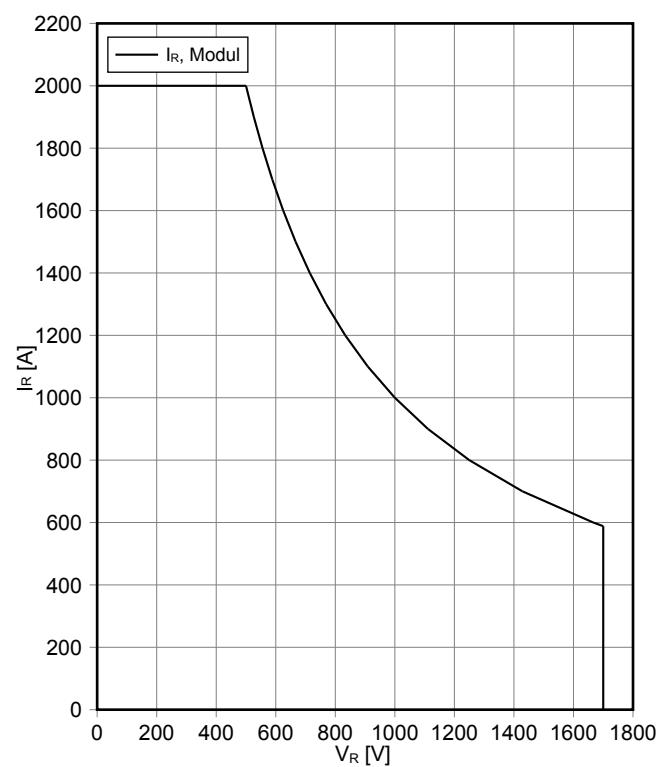
瞬态热阻抗 二极管，制动-斩波器

transient thermal impedance Diode, Brake-Chopper

 $Z_{thJC} = f(t)$ 

安全工作区 二极管，制动-斩波器 (SOA)

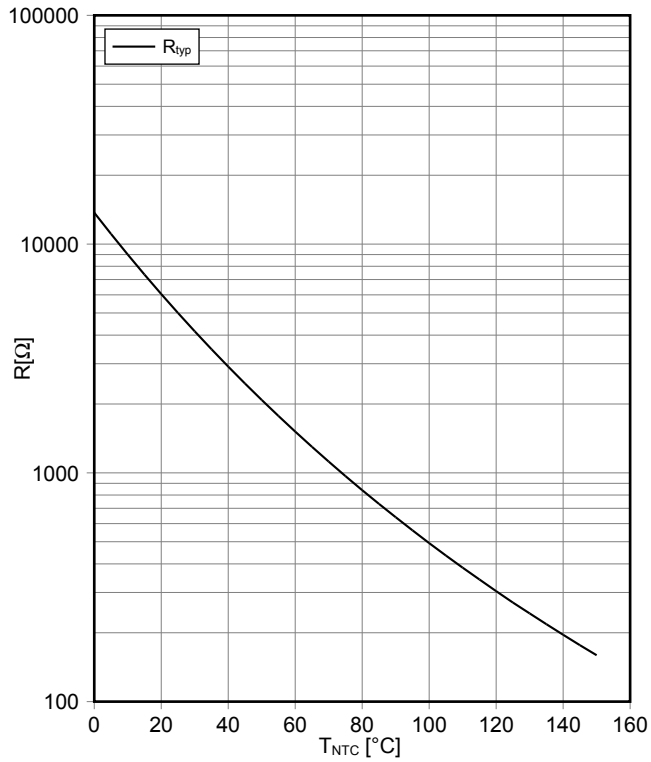
safe operation area Diode, Brake-Chopper (SOA)

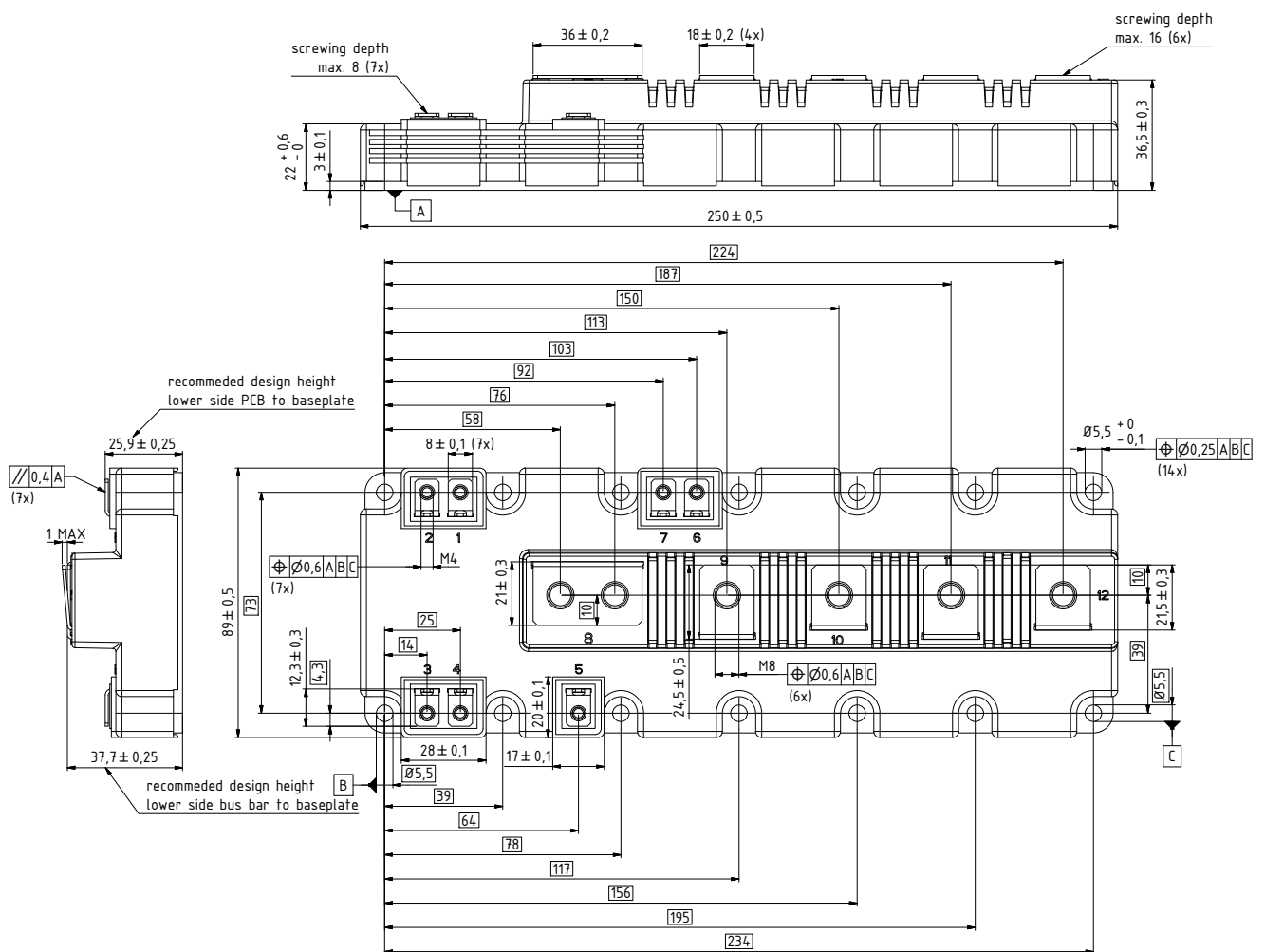
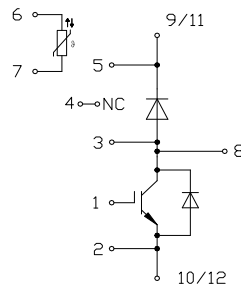
 $I_R = f(V_R)$ $T_{vj} = 150^\circ C$ 

负温度系数热敏电阻 温度特性

NTC-Thermistor-temperature characteristic (typical)

$R = f(T)$





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